Microsemi LAWRENCE

TECHNICAL DATA

PNP POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/535

Devices		*Qualified Level*
2N5003	**2N5005**	**JAN JANTX JANTXV**

MAXIMUM RATINGS

Ratings	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Collector-Base Voltage	V_{CBO}	100	Vdc
Emitter-Base Voltage	V_{EBO}	5.5	Vdc
Collector Current	I_C I_C (3)	5.0 10	Adc
Total Power Dissipation @ $T_A = +25^0C$ (1) @ $T_C = +25^0C$ (2)	P_T	2.0 58	W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	^0C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.0	$^0C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	88	$^0C/W$

1) Derate linearly 11.4 mW/^{0}C for $T_A > +25^0C$
2) Derate linearly 331 mW/^{0}C for $T_C > +25^0C$
3) This value applies for $P_W \leq 8.3$ ms, duty cycle $\leq 1\%$

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*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_C = 25^0C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage $I_C = 100$ mAdc,	$V_{(BR)CEO}$	80		Vdc
Collector-Emitter Cutoff Current $V_{CE} = 40$ Vdc, $I_B = 0$	I_{CEO}		50	µAdc
Collector-Emitter Cutoff Current $V_{CE} = 60$ Vdc, $V_{BE} = 0$ $V_{CE} = 100$ Vdc, $V_{BE} = 0$	I_{CES}		1.0 1.0	µAdc mAdc
Emitter-Base Cutoff Current $V_{BE} = 4.0$ Vdc, $I_C = 0$ $V_{BE} = 5.5$ Vdc, $I_C = 0$	I_{EBO}		1.0 1.0	MAdc MAdc

ELECTRICAL CHARACTERISTICS (Con't)

Characteristics		Symbol	Min.	Max.	Unit
ON CHARACTERISTICS					
Forward-Current Transfer Ratio					
I_C = 50 mAdc, V_{CE} = 5.0 Vdc	2N5003	h_{FE}	20	90	
I_C = 2.5 Adc, V_{CE} = 5.0 Vdc			30		
I_C = 5.0 Adc, V_{CE} = 5.0 Vdc			20		
I_C = 50 mAdc, V_{CE} = 5.0 Vdc	2N5005		50	200	
I_C = 2.5 Adc, V_{CE} = 5.0 Vdc			70		
I_C = 5.0 Adc, V_{CE} = 5.0 Vdc			40		
Base-Emitter Voltage Non-saturated V_{CE} = 5.0 Adc, I_C =2.5 Adc		V_{BE}		1.45	Vdc
Collector-Emitter Saturation Voltage I_C = 2.5 Adc, I_B = 250 mAdc I_C = 5.0 Adc, I_B = 500 mAdc		$V_{CE(sat)}$		0.75 1.5	Vdc
Base-Emitter Saturation Voltage I_C = 2.5 Adc, I_B = 250 mAdc I_C = 5.0 Adc, I_B = 500 mAdc		$V_{BE(sat)}$		1.45 2.2	Vdc
DYNAMIC CHARACTERISTICS					
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio 2N5003 I_C = 100 mAdc, V_{CE} = 5.0 Vdc, f = 10 MHz	2N5005	h_{fe}	2.0 50		
Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio 2N5003 I_C = 500 mAdc, V_{CE} = 5.0 Vdc, f = 10 MHz	2N5005	h_{fe}	6.0 7.0		
Output Capacitance V_{CB} = 10 Vdc, I_E = 0, f = 1 MHz		C_{obo}		250	PF
SWITCHING CHARACTERISTICS					
Turn-On Time I_C = 5 Adc; I_{B1}= 500 mAdc		t_{on}		0.5	µs
Storage Time	I_{B2}= -500 mAdc	t_s		1.4	µs
Fall Time	$V_{BE(OFF)}$ = 3.7 Vdc	t_f		0.5	µs
Turn-Off Time R_L = 6 Ω		t_{off}		1.5	µs

SAFE OPERATING AREA

DC Tests

T_C = +25^{0}C, V_{CE} = 0, t_P = 1 second 1 Cycle

Test 1

V_{CE} = 12 Vdc, I_C = 5 Adc

Test 2

V_{CE} = 32 Vdc, I_C = 1.7 Adc

Test 3

V_{CE} = 80 Vdc, I_C = 100 mAdc